

**HALOGEN** 

FREE

# HEXFRED® Ultrafast Soft Recovery Diode, 6 A



PRIMARY CHARACTERISTICS									
I <sub>F(AV)</sub>	6 A								
$V_{R}$	1200 V								
V <sub>F</sub> at I <sub>F</sub>	2.4 V								
t <sub>rr</sub> (typ.)	26 ns								
T <sub>J</sub> max.	150 °C								
Package	D <sup>2</sup> PAK (TO-263AB)								
Circuit configuration	Single								

#### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- · Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C



#### **BENEFITS**

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

VS-HFA06TB120S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 6 A continuous current, the VS-HFA06TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the t<sub>b</sub> portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA06TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V <sub>R</sub>		1200	V					
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	6						
Single pulse forward current	I <sub>FSM</sub>		80	Α					
Maximum repetitive forward current	I <sub>FRM</sub>		24						
Maximum newer discination	В	T <sub>C</sub> = 25 °C	62.5	W					
Maximum power dissipation	$P_{D}$	T <sub>C</sub> = 100 °C	25	VV					
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C					





<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)										
PARAMETER	ARAMETER SYMBOL TEST CONDITIONS				MAX.	UNITS				
Cathode to anode breakdown voltage	$V_{BR}$	I <sub>R</sub> = 100 μA	1200	-	i					
	V <sub>FM</sub>	I <sub>F</sub> = 6.0 A	-	2.7	3.0	V				
Maximum forward voltage		I <sub>F</sub> = 12 A	-	3.5	3.9					
		I <sub>F</sub> = 6.0 A, T <sub>J</sub> = 125 °C	-	2.4	2.8	]				
Maximum reverse	I <sub>RM</sub>	$V_R = V_R$ rated	-	0.26	5.0					
leakage current		T <sub>J</sub> = 125 °C, V <sub>R</sub> = 0.8 x V <sub>R</sub> rated	-	110	500	μΑ				
Junction capacitance	C <sub>T</sub>	C <sub>T</sub> V <sub>R</sub> = 200 V		9.0	14	pF				
Series inductance L <sub>S</sub> Measured lead to lead 5 mm from package body		-	8.0	-	nH					

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	A/ $\mu$ s, $V_R = 30 \text{ V}$	-	26	-	ns		
Reverse recovery time	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	53	80			
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	87	130			
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	4.4	8.0	- A		
reak recovery current	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C	$I_F = 6.0 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$	-	5.0	9.0			
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C	$V_{R} = 200 \text{ V}$	-	116	320			
neverse recovery charge	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	233	585			
Peak rate of recovery current	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	180	-			
during t <sub>b</sub>	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	100	-	A/µs		

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	2.0					
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	K/W				
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth, and greased	-	0.5	-					
Weight			-	2.0	-	g				
vveigni			-	0.07	-	oz.				
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	HFA06TB120S							

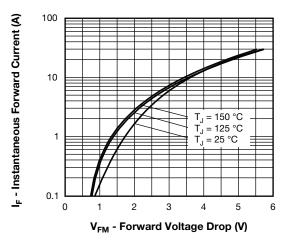


Fig. 1 - Typical Forward Voltage Drop Characteristics

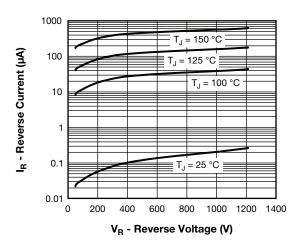


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

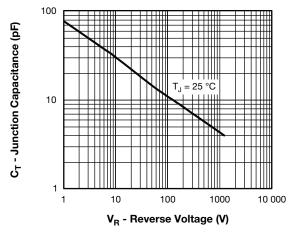


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

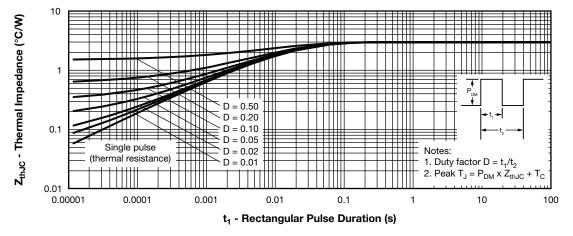
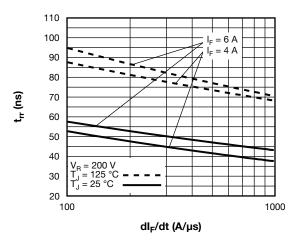


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics



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Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

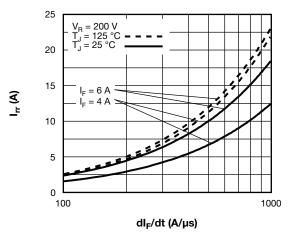


Fig. 6 - Typical Recovery Current vs. dI<sub>F</sub>/dt

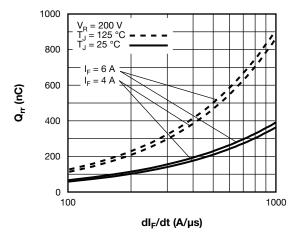


Fig. 7 - Typical Stored Charge vs.  $dI_F/dt$ 

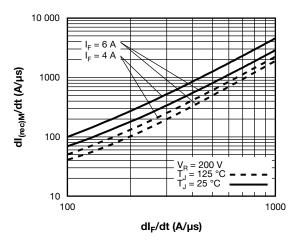
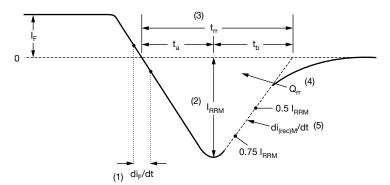


Fig. 8 - Typical  $dI_{(rec)M}/dt$  vs.  $dI_F/dt$ 



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $\rm Q_{rr}$  area under curve defined by  $\rm t_{rr}$  and  $\rm I_{RRM}$

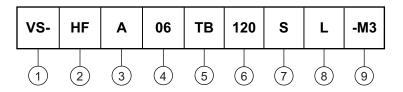
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 9 - Reverse Recovery Waveform and Definitions

#### ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- 2 HEXFRED® family
- Process designator: A = electron irradiated
- 4 Current rating (06 = 6 A)
- 5 Package outline (TB = TO-220, 2 leads)
- 6 Voltage rating (120 = 1200 V)
- 7  $S = D^2PAK (TO-263AB)$
- None = tube (50 pieces)
  - L = tape and reel (left oriented)
  - R = tape and reel (right oriented)
- 9 Environmental digit:
  - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free



## **VS-HFA06TB120S-M3**

# Vishay Semiconductors

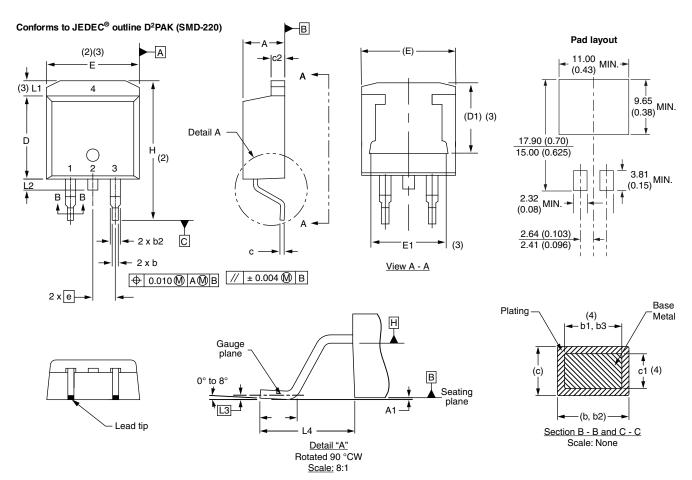
ORDERING INFORMATION (Example)									
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION							
VS-HFA06TB120S-M3	50	Antistatic plastic tube							
VS-HFA06TB120SR-M3	800	13" diameter reel							
VS-HFA06TB120SL-M3	800	13" diameter reel							

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96164					
Part marking information	www.vishay.com/doc?95444					
Packaging information	www.vishay.com/doc?96424					



### D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164



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